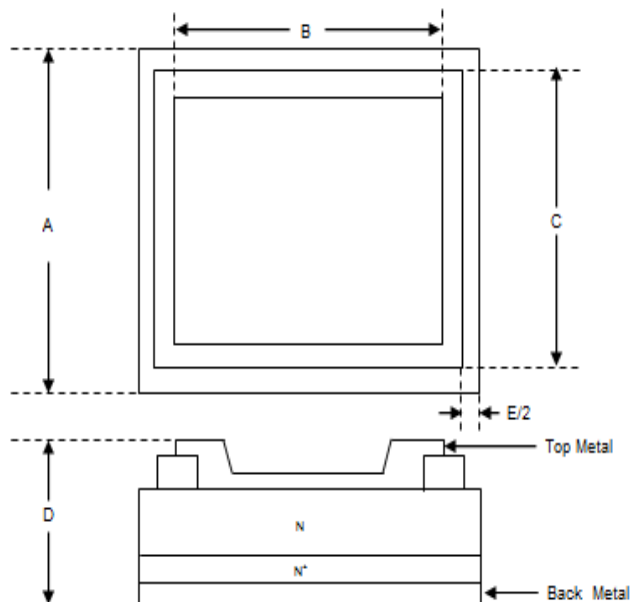


Planar Schottky Barrier Diode Wafer (PSBD)



Item	Dimensions	
	um	mil
Die Size (A)	2846	112
Top Metal Pad Size (B)	2740	107
Passivation Seal (C)	2786	109.7
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	60	2.36
Other Informations		
Wafer Size	6"	
Gross Die	1953	
Top Metal	Ag	
Back Metal	Ag	

Electrical Characteristics @TA=25°C				
Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.05mA	V_{RRM}	200	210	V
Maximum Average Forward Rectified Current	I_o	20	-	A
Forward Voltage Drop, @ $I_F=3A$ @ $I_F=10A$ @ $I_F=15A$ @ $I_F=20A$	V_F	0.84 0.88 0.92	0.73 - - -	V
Maximum Reverse Current at Rated V_{RRM}	I_R	5	1	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	250	-	A
Operating Temperature Range	T_J	-50 to +175	-	°C
Storage Temperature Range	T_{STG}	-50 to +175	-	°C